

## LESD8LU5.0T5G ESD PROTECTION DIODE

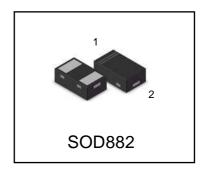
### **Discription**

The LESD8LU5.0T5G is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, digital cameras and many other portable applications where board space is at a premium.

### **Applications**

- l Cellular phones audio
- l Digital cameras
- l Portable applicationss
- I mobile telephone

## LESD8LU5.0T5G





### **Features**

- Small Body Outline Dimensions: 1.0 mm x 0.6 mm
- Low Body Height: 0.5 mm
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices
- We declare that the material of product compliance with RoHS requirements.

### **Ordering information**

Device	Marking	Shipping
LESD8LU5.0T5G	E5	10000/Tape&Reel

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air discharge Contact discharge		±15 ±8	kV kV
ESD Voltage Per Human Body Model		16	kV
Total Power Dissipation on FR-5 Board (Note 1)	PD	200	mW
@ T <sub>A</sub> =25℃			
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	$^{\circ}$
Lead Solder Temperature - Maximum (10	TL	260	$^{\circ}$
Second Duration)			

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0\*0.75\*0.62 in.

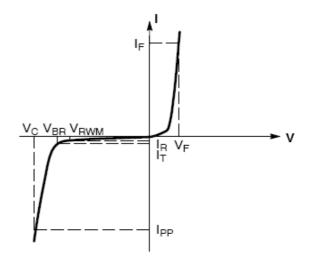


## LESD8LU5.0T5G

#### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current	
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>	
V <sub>RWM</sub>	Working Peak Reverse Voltage	
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>	
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>	
I <sub>T</sub>	Test Current	
I <sub>F</sub>	Forward Current	
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>	
P <sub>pk</sub>	Peak Power Dissipation	
С	Max. Capacitance @V <sub>R</sub> = 0 and f = 1 MHz	



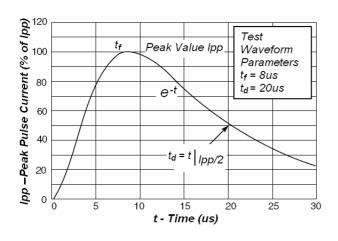
Uni-Directional TVS

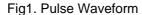
### **ELECTRICAL CHARACTERISTICS**

	V <sub>RWM</sub> (V)	I <sub>R</sub> (μΑ) @ V <sub>RWM</sub>	V <sub>BR</sub> (V) @ Ի (Note 2)	Ι <sub>Τ</sub>	V <sub>C</sub> (V) @ I <sub>PP</sub> = 1 A (Note 3)	V <sub>C</sub> (V) @MAX I <sub>PP</sub> (Note 3)	I <sub>PP</sub> (A) (Note 3)	P <sub>PK</sub> (W) (Note 3)	C (t	oF)
Device	Max	Max	Min	mA	Max	Max	Max	Max	Тур	Max
LESD8LU5.0T5G	5	0.5	6	1.0	10	15	4	60	0.5	0.9

Other voltage available upon request.

- 2.  $V_{BR}$  is measured with a pulse test current IT at an ambient temperature of 25  $^{\circ}{\!\!\!^{\circ}}{\!\!\!^{\circ}}$
- 3. Surge current waveform per Figure 1.





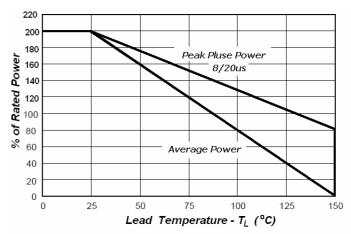


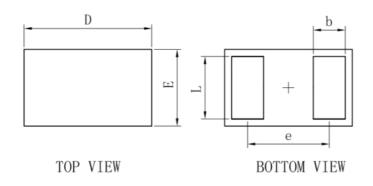
Fig2.Power Derating Curve



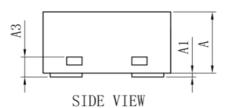
# LESD8LU5.0T5G

# **SOD882**

Package Outline Dimension

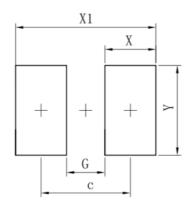


S0D882				
Dim	Min	Тур	Max	
D	0.95	1.00	1.05	
Е	0.55	0.60	0.65	
е	-	0.64	-	
L	0.44	0.49	0.54	
b	0.20	0. 25	0.30	
A	0.43	0.48	0.53	
A1	0	-	0.05	
A3 0. 127REF.				
All Dimensions in mm				



## Suggested Pad layout

# S0D882



Dimensions	(mm)
С	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70